

UTC UNISONIC TECHNOLOGIES CO., LTD

TF215

Preliminary

JFET

N-CHANNEL JUNCTION FIELD EFFECT TRANSISTOR

DESCRIPTION

The UTC TF215 is an N-channel junction field effect transistor, and it can be specially used in electronic condenser microphone.

FEATURES

* Good voltage characteristics and transient characteristics.



ORDERING INFORMATION

Ordering Number		Deekage		Assign	Decking		
		Раскаде	1	2	3	Раскіпд	
TF215G-x-AN3-R		SOT-523	S	D	G	Tape Reel	
Note: Pin Assignment: S: Source D: Drain G: Gate							
ТF215 <u>Ģ-</u> ұ- <u>АŅ3-</u> Ŗ							
(1)Packing Type	(1) F	R: Tape Reel					
(2)Package Type (2) AN3: SOT-523							
(3)Rank	(3) x: refer to Classification of I_{DSS}						
(4)Green Package	(4) G: Halogen Free and Lead Free						

MARKING

TF215-E3	TF215-E4	TF215-E5			
E E					
E3	E4	E5			

■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Gate to Drain Voltage	V _{GDO}	-20	V
Gate Current	l _G	10	mA
Drain Current	I _D	1	mA
Power Dissipation	PD	100	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
G-D Breakdown Voltage	BV _{GDO}	Ι _G =-100μΑ	-20			V
Gate Off Voltage	$V_{GS(OFF)}$	V _{DS} =5.0V, I _D =1µA	-0.2	-0.6	-1.0	V
Drain Current	I _{DSS}	V _{DS} =5.0V, V _{GS} =0	100		350	μA
Forward Transfer Admittance	YFS	V _{DS} =2.0V, V _{GS} =0, f=1KHz	0.8	1.2		mS
Input Capacitance	CISS	V _{DS} =5.0V, V _{GS} =0, f=1MHz		3.5		pF
Reverse Transfer Capacitance	CRSS	V _{DS} =5.0V, V _{GS} =0, f=1MHz		0.65		рF
Voltage Gain	Gv	V _{IN} =10mV, f=1KHz		-3.0		dB
Reduced Voltage Characteristic	∆Gvv	V _{IN} =10mV, f=1KHz V _{CC} =4.5→1.5V		-1.2	-3.5	dB
Frequency Characteristic	∆G _{Vf}	f=1KHz~110Hz			-1.0	dB
Input Resistance	Z _{IN}	f=1KHz	25			MΩ
Output Resistance	Zo	f=1KHz		1000		Ω
Total Harmonic Distortion	THD	V _{IN} =30mV, f=1KHz		1.2		%
Output Noise Voltage	V _{NO}	V _{IN} =0, A Curve			-110	dB

CLASSIFICATION OF IDSS

RANK	E3	E4	E5
RANGE	100-170	140-240	210-350



■ TEST CIRCUIT (T_A=25°C)



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